

SWITCHING REGURATOR APPLICATIONS

Features

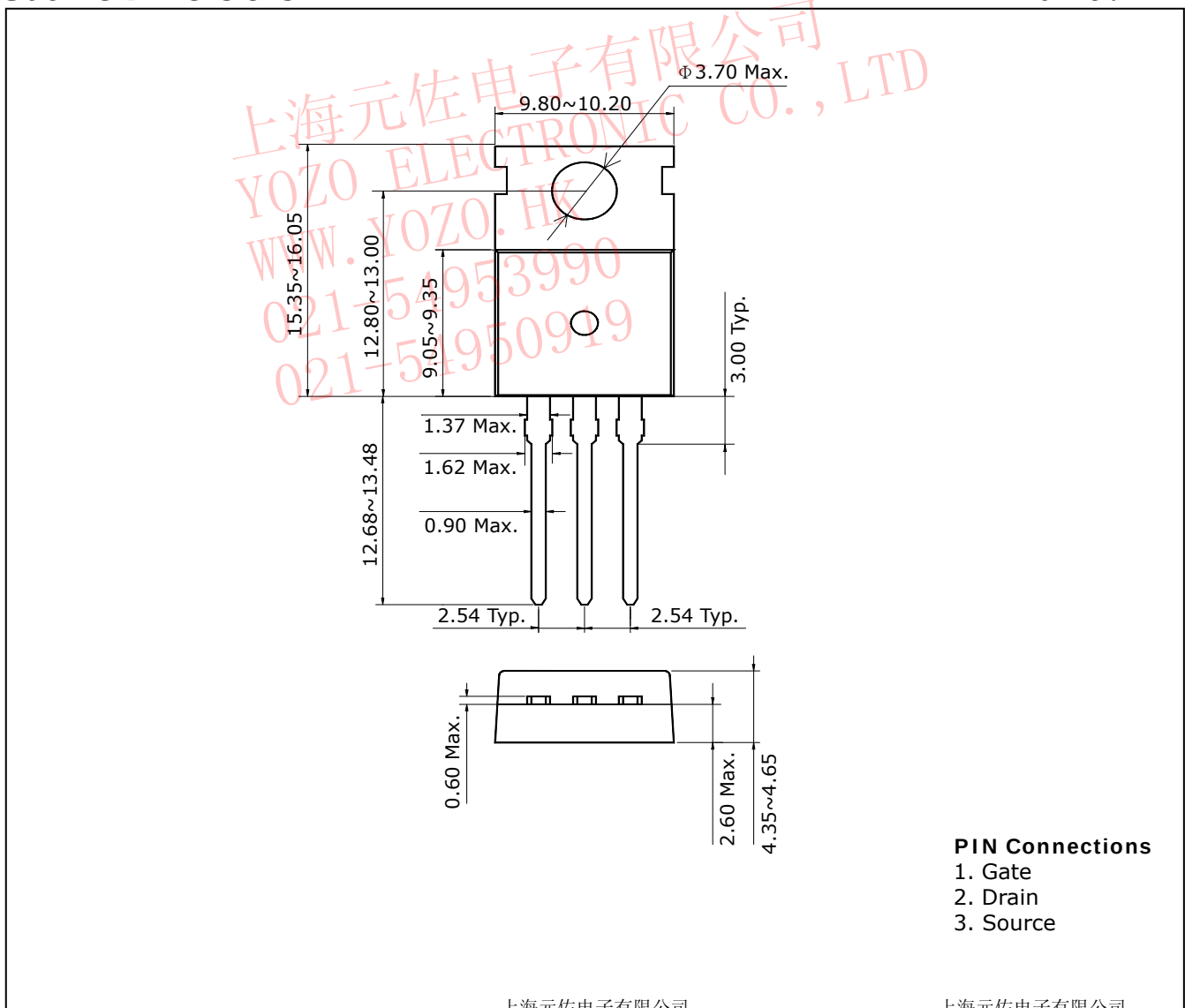
- High Voltage: $BV_{DSS}=75V(\text{Min.})$
- Low C_{rss} : $C_{rss}=220pF(\text{Typ.})$
- Low gate charge : $Qg=80nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=15m\Omega(\text{Max.})$

Ordering Information

Type NO.	Marking	Package Code
STK7575P	STK7575	TO-220AB-3L

Outline Dimensions

unit : mm



Absolute maximum ratings (Tc=25°C)

Characteristic	Symbol	Rating	Unit
Drain-Source voltage	V_{DS}	75	V
Gate-Source voltage	V_{GS}	±20	V
Continuous Drain current (Tc=25°C)	I_D	75	A
Continuous Drain current (Tc=100°C)	I_D	57.8	A
Drain Current-Pulsed ①	I_{DM}	300	A
Power Dissipation (Tc=25°C)	P_D	220	W
Single Pulsed Avalanche Energy ②	E_{AS}	1310	mJ
Avalanche current ①	I_{AR}	75	A
Repetitive Avalanche Energy ①	E_{AR}	17.3	mJ
Junction temperature	T_J	175	°C
Storage temperature range	T_{stg}	-55~175	

Thermal Resistance

Characteristic	Symbol	Typ.	Max	Units
Junction to Case	$R_{th(J-C)}$	-	0.68	°C/W
Junction to Ambient	$R_{th(J-a)}$	-	62.5	

Electrical Characteristics (Tc=25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-Source breakdown voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0$	75	-	-	V
Gate-Threshold voltage	$V_{GS(th)}$	$I_D=250\mu A, V_{DS}=V_{GS}$	2.0	-	4.0	V
Drain-source leakage current	I_{DSS}	$V_{DS}=75V, V_{GS}=0V$	-	-	10	μA
Gate-source leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
Drain-Source on-resistance ③	$R_{DS(ON)}$	$V_{GS}=10V, I_D=37.5A$	-	12	15	m Ω
Forward transfer admittance ③	g_{fs}	$V_{DS}=20V, I_D=37.5A$	-	15	-	S
Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V, f=1MHz$	-	2540	3210	pF
Output capacitance	C_{oss}		-	950	1200	
Reverse transfer capacitance	C_{rss}		-	220	275	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=40V, I_D=75A$ $R_G=25\Omega$ ③④	-	40	80	ns
Rise time	t_r		-	230	460	
Turn-off delay time	$t_{d(off)}$		-	170	340	
Fall time	t_f		-	190	330	
Total gate charge	Q_g	$V_{DS}=60V, V_{GS}=10V,$ $I_D=75A$ ③④	-	80	105	nC
Gate-source charge	Q_{gs}		-	16	-	
Gate-drain("Miller")charge	Q_{gd}		-	30	-	

Source-Drain Diode Ratings and Characteristics (Tc=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Units
Continuous source current	I_S	Integral reverse diode in the MOSFET	-	-	75	A
Pulsed-source current ①	I_{SM}		-	-	300	
Diode forward voltage ③	V_{SD}	$V_{GS}=0V, I_S=75A$	-	-	1.5	V
Reverse recovery time	t_{rr}	$I_S=75A$ $di_F/dt=100A/us$ ③	-	90	-	ns
Reverse recovery charge	Q_{rr}		-	250	-	μC

Note ;

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ② $L=0.32mH, I_{AS}=75A, V_{DD}=25V, R_G=25\Omega$, starting $T_J=25^\circ C$
- ③ Pulse Test : Pulse Width < 300us, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

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Fig. 1 $I_D - V_{DS}$

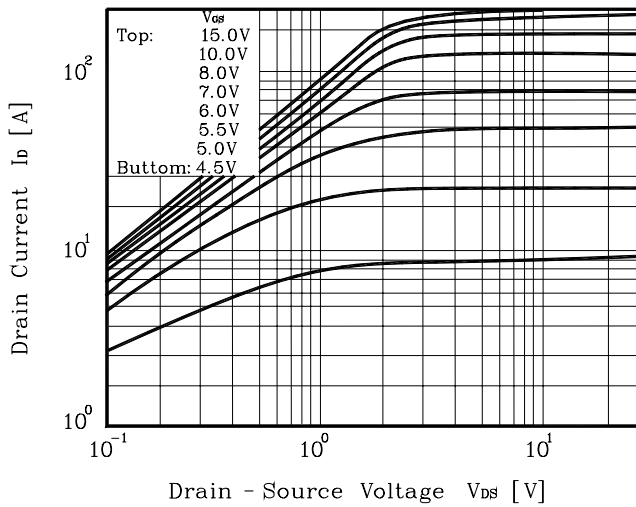


Fig. 2 $I_D - V_{GS}$

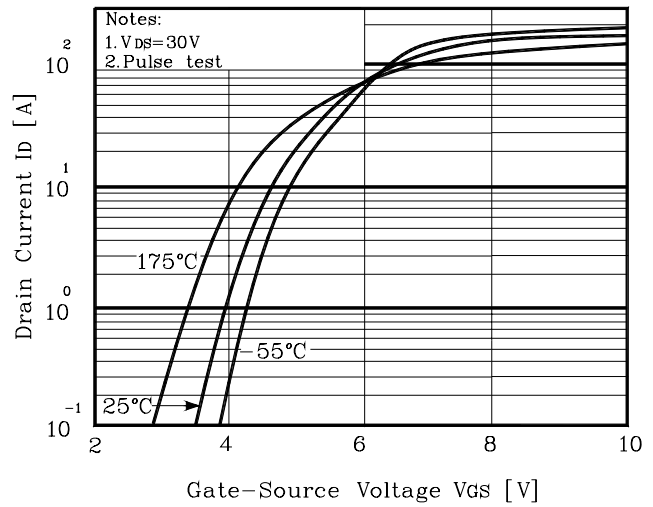


Fig. 3 $R_{DS(on)} - I_D$

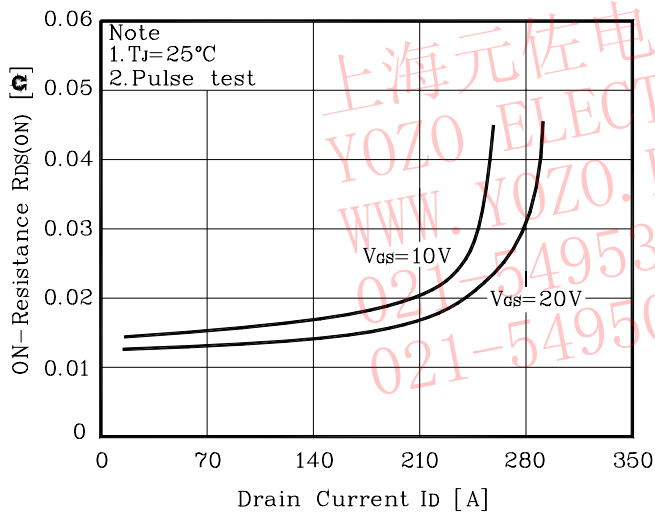


Fig. 4 $I_S - V_{SD}$

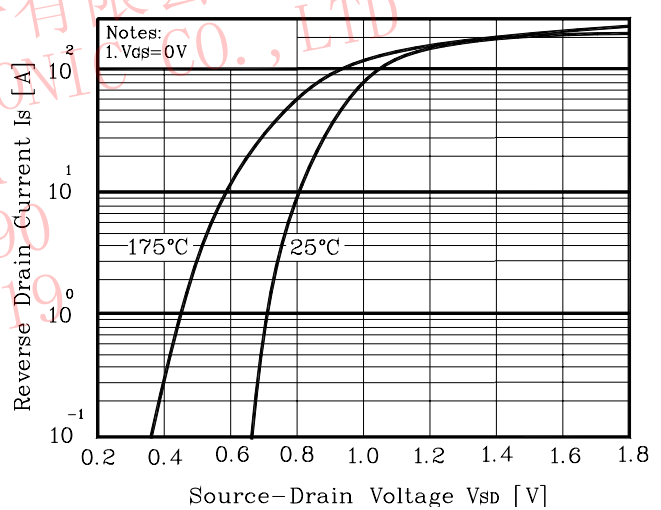


Fig. 5 Capacitance - V_{DS}

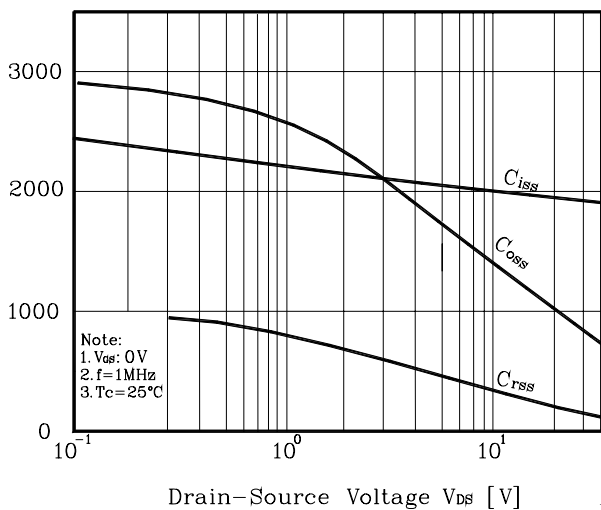


Fig. 6 $V_{GS} - Q_G$

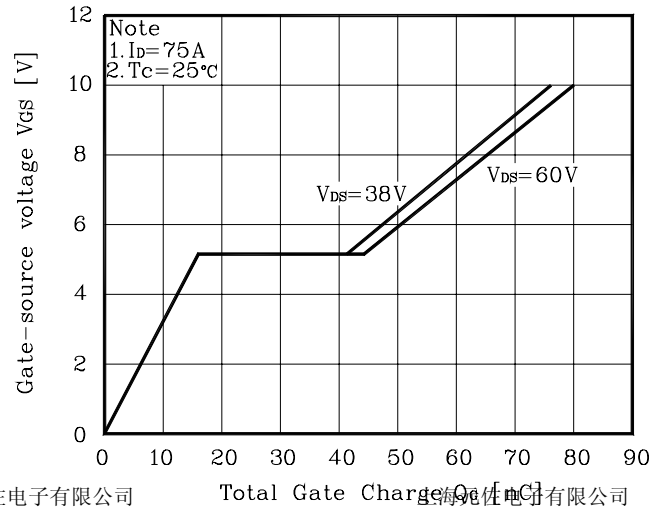


Fig. 7 $V_{DS} - T_J$

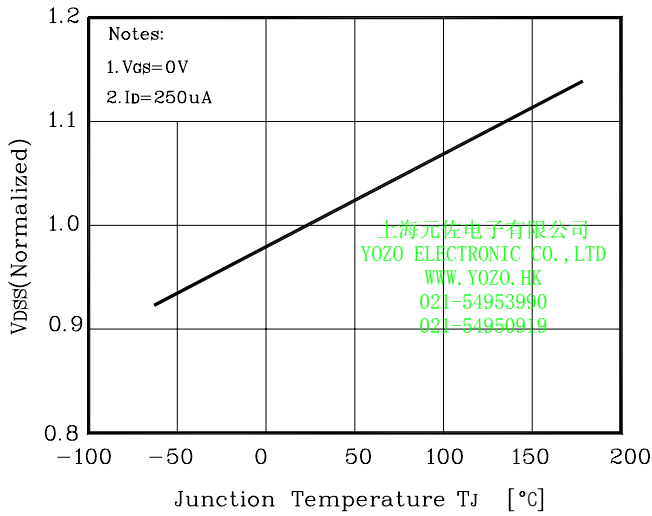


Fig.8 $R_{DS(on)} - T_J$

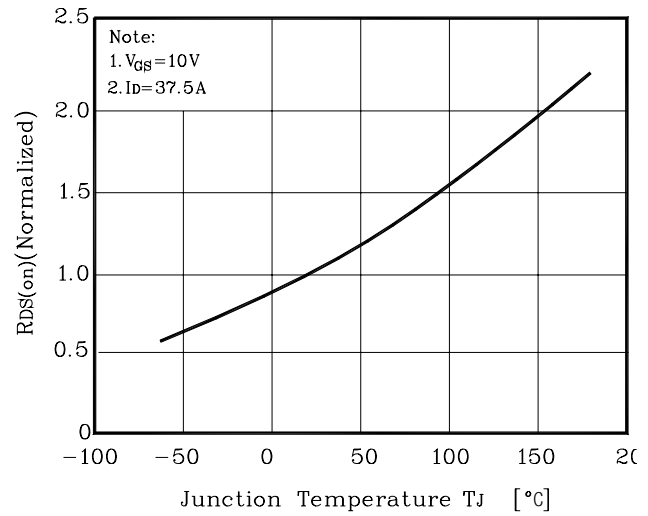


Fig. 9 $I_D - T_C$

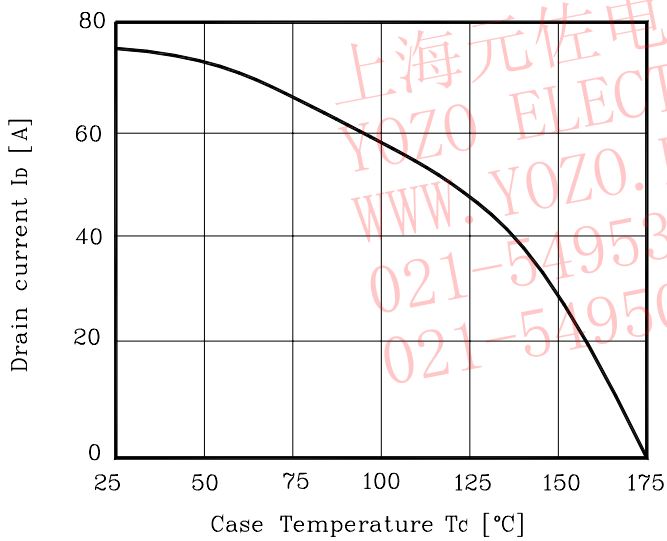
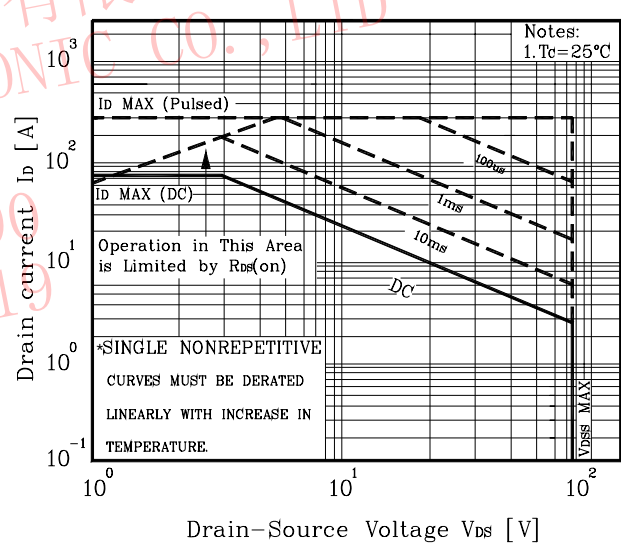


Fig. 10 Safe Operating Area



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Fig. 10 Gate Charge Test Circuit & Waveform

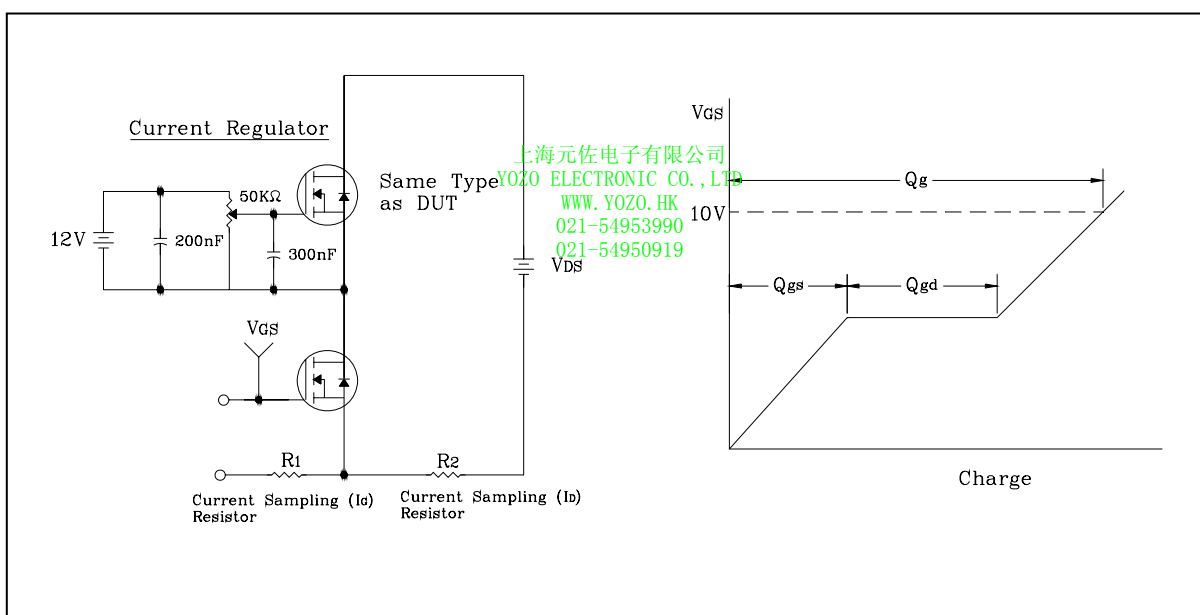


Fig. 11 Resistive Switching Test Circuit & Waveform

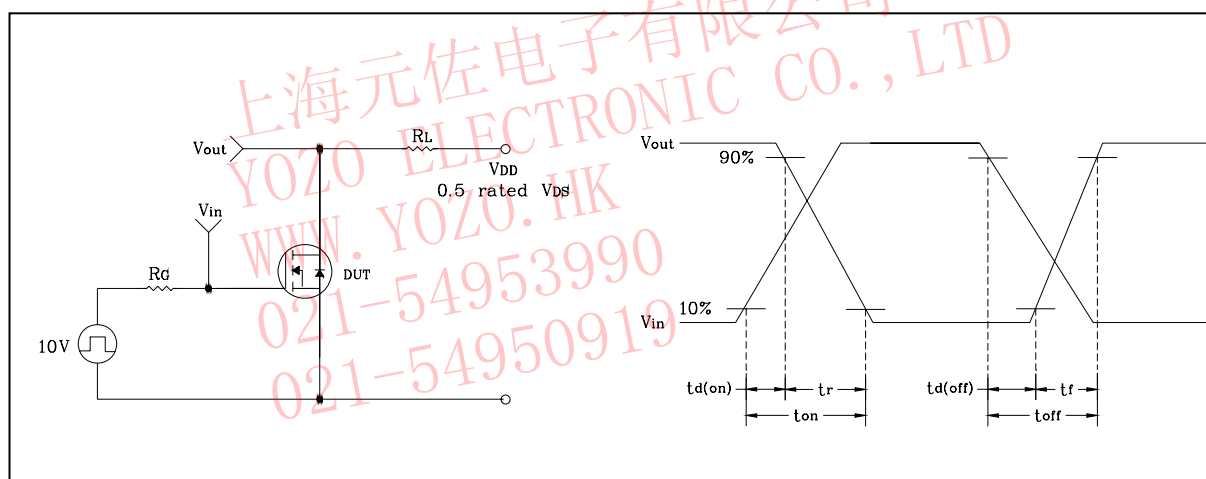
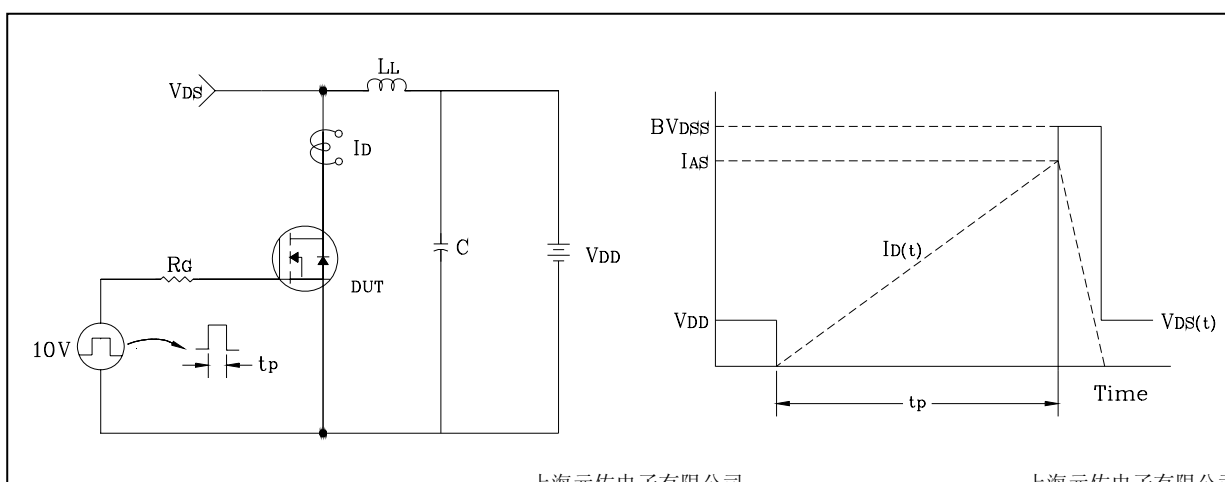


Fig. 12 E_{AS} Test Circuit & Waveform



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-. dv/dt controlled by "Rd"
-. Is controlled by Duty Factor "D"

